

80V PNP MEDIUM POWER TRANSISTOR IN SOT89

Features

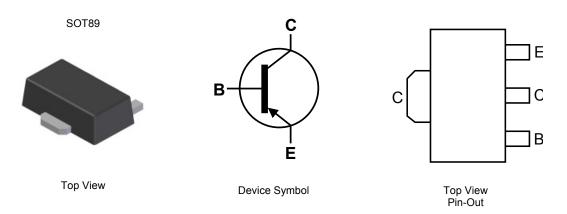
- BV_{CEO} > -80V
- I_C = -1A High Continuous Current
- Low saturation voltage V_{CE(sat)} < -250mV @ -150mA
- Complementary type BSR43
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish, Solderable per MIL-STD-202, Method 208 (a)
- Weight: 0.052 grams (Approximate)

Application

- Load management functions
- Solenoid, relay and actuator drivers
- DC DC modules



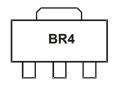
Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
BSR33TA	AEC-Q101	BR4	7	12	1,000
BSR33QTA	Automotive	BR4	7	12	1.000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q10x qualified and are PPAP capable. Automotive, AEC-Q10x and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



BR4 = Product Type Marking Code





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-90	V
Collector-Emitter Voltage	V_{CEO}	-80	V
Emitter-Base Voltage	V_{EBO}	-5	V
Continuous Collector Current	Ic	-1	Α
Peak Pulse Current	I _{CM}	-2	Α
Peak Base Current	I _{BM}	-200	mA

Thermal Characteristics (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
	(Note 6)		1	
Power Dissipation	(Note 7)	P_{D}	1.5	W
	(Note 8)		2.1	
	(Note 6)		125	
Thermal Resistance, Junction to Ambient Air	(Note 7)	Roja	83	°C/W
	(Note 8)		60	
Thermal Resistance, Junction to Lead	(Note 9)	R₀JL	13	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C	

ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 6. For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

- 7. Same as note (6), except the device is mounted on 25mm x 25mm 1oz copper.

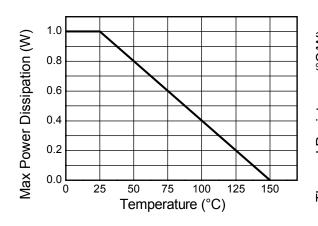
 8. Same as note (6), except the device is mounted on 50mm x 50mm 1oz copper.

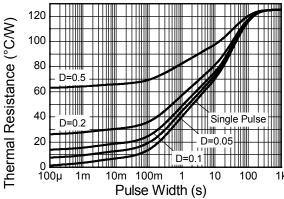
 9. Thermal resistance from junction to solder-point (on the exposed collector pad).

 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





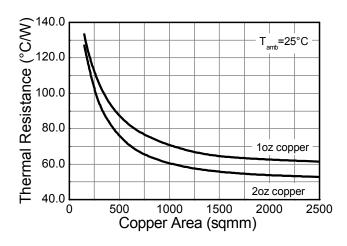
Derating Curve

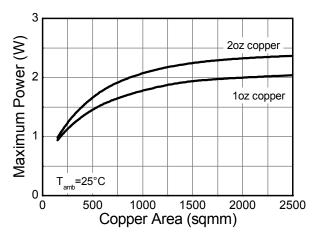
Defating curve

100
Single Pulse. T = 25°C | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100

Transient Thermal Impedance

Pulse Power Dissipation









Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	-90	-	ı	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	-80	-	ı	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	-5	_	ı	V	I _E = -100μA
Collector Cutoff Current	I _{CBO}	_	_	-100 -50	nΑ μΑ	$V_{CB} = -60V$ $V_{CB} = -60V$, $T_{J} = +150$ °C
DC current transfer Static ratio (Note 11)	h _{FE}	30 100 50	- - -	- 300 -	-	I _C = -100μA, V _{CE} = -5V I _C = -100mA, V _{CE} = -5V I _C = -500mA, V _{CE} = -5V
Collector-Emitter Saturation Voltage (Note 11)	$V_{\text{CE(sat)}}$	-	-	-0.25 -0.5	V	I _C = -150mA, I _B = -15mA I _C = -500mA, I _B = -50mA
Base-Emitter Saturation Voltage (Note 11)	$V_{BE(sat)}$	-	-	-1.0 -1.2	V	I _C = -150mA, I _B = -15mA I _C = -500mA, I _B = -50mA
Transitional Frequency	f⊤	100	-	ı	MHz	$I_C = -50 \text{mA}, V_{CE} = -10 \text{V}$ f = 35MHz
Output capacitance	C_obo	-	-	20	pF	V _{CB} = -10V, f = 1MHz
Input Capacitance	C_{ibo}	-	_	120	pF	$V_{CB} = -0.5V, f = 1MHZ$
Turn-On Time	Ton	_	_	500	ns	V_{CC} =-20V, I_{C} = -100mA
Turn-Off Time	T_{off}	_	_	650	ns	$I_{B1} = I_{B2} = -5mA$

Note:

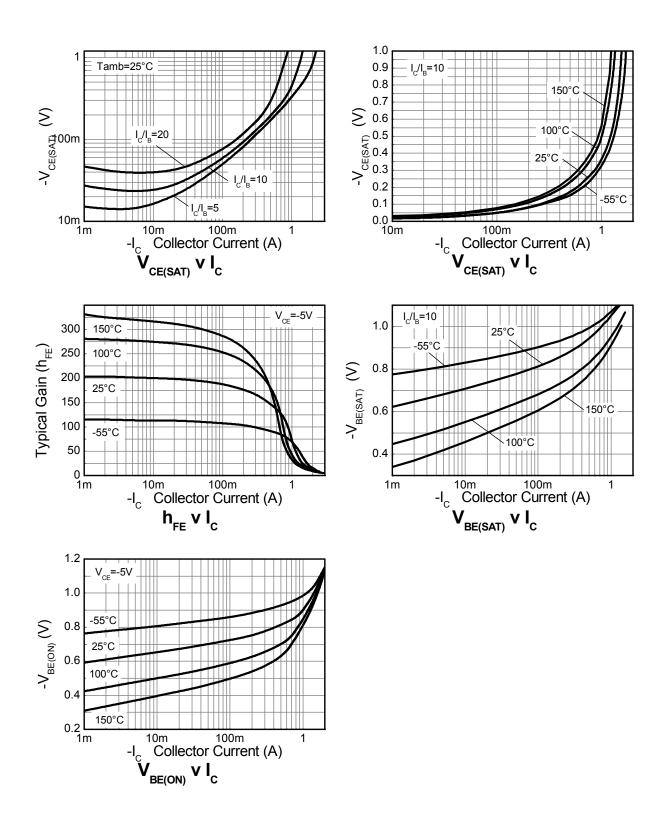
11. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



November 2013

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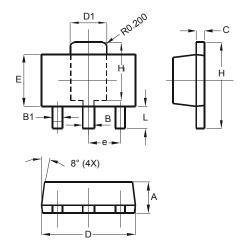
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)





Package Outline Dimensions

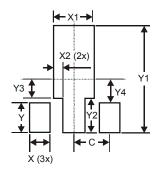
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT89				
Dim	Min	Max		
Α	1.40	1.60		
В	0.44	0.62		
B1	0.35	0.54		
С	0.35	0.44		
D	4.40	4.60		
D1	1.62	1.83		
Е	2.29	2.60		
е	1.50 Typ			
Н	3.94	4.25		
H1	2.63	2.93		
L	0.89	1.20		
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
X	0.900
X1	1.733
X2	0.416
Y	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
С	1 500





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